



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

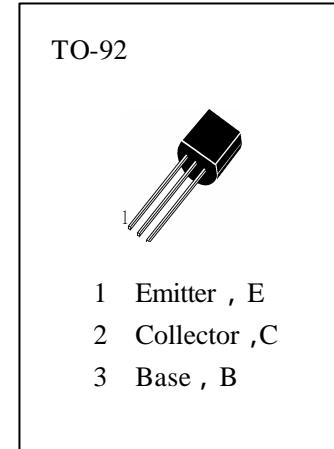
H3202

APPLICATIONS

General Purpose And Switching Applications..

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation.....	500mW
V_{CBO} —Collector-Base Voltage.....	35V
V_{CEO} —Collector-Emitter Voltage.....	30V
V_{EBO} —Emitter-Base Voltage.....	5V
I_c —Collector Current.....	500mA
I_b —Base Current.....	100mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	35			V	$I_c=100 \mu A, I_e=0$
BVCEO	Collector-Emitter Breakdown Voltage	30			V	$I_c=1mA, I_b=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_e=100 \mu A, I_c=0$
HFE(1)	DC Current Gain	70		240		$V_{ce}=1V, I_c=100mA$
HFE(2)	DC Current Gain	25				$V_{ce}=6V, I_c=400mA$
VCE(sat)	Collector- Emitter Saturation Voltage		0.1	0.25	V	$I_c=20mA, I_b=2mA$
VBE(ON)	Base-Emitter On Voltage		0.8	1.0	V	$V_{ce}=1V, I_c=100mA$
ICBO	Collector Cut-off Current			100	nA	$V_{cb}=35V, I_e=0$
IEBO	Emitter Cut-off Current			100	nA	$V_{eb}=5V, I_c=0$
f _r	Current Gain-Bandwidth Product		300		MHz	$V_{ce}=6V, I_c=20mA$
C _{ob}	Output Capacitance		7.0		pF	$V_{cb}=6V, I_e=0, f=1MHz$

h_{FE} Classification

O

70—140

Y

120—240